depositing a second metal on the glass substrate, a height of the second metal being smaller than a depth of the groove;

E1 (concluded)

removing the photoresist pattern on the glass substrate and the second metal on the photoresist other than in the groove; and

forming the first metal on the second metal in the groove by submerging the glass substrate in the mixed solution.

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12. (Amended) The method of claim 1, further comprising:

forming a first insulating layer over the glass substrate to cover the first metal;

E2

forming a semiconductor layer on the first insulating layer;

forming source and drain electrodes on the semiconductor layer;

forming a second insulating layer over the whole glass substrate covering the source and drain electrode, the second insulating layer including a contact hole on a portion of the drain electrode; and

forming a pixel electrode on the second insulating layer, the pixel electrode electrically connecting with the drain electrode through the contact hole.
